MC74VHCT00A

Quad 2-Input NAND Gate

The MC74VHCT00A is an advanced high speed CMOS 2-input NAND gate fabricated with silicon gate CMOS technology. It achieves high speed operation while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The device input is compatible with TTL-type input thresholds and the output has a full 5 V CMOS level output swing. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic-level translator from 3.0 V CMOS logic to 5.0 V CMOS Logic or from 1.8 V CMOS logic to 3.0 V CMOS Logic while operating at the high-voltage power supply.

The MC74VHCT00A input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the MC74VHCT00A to be used to interface 5 V circuits to 3 V circuits. The output structures also provide protection when V_{CC} = 0 V. These input and output structures help prevent device destruction caused by supply voltage - input/output voltage mismatch, battery backup, hot insertion, etc.

- High Speed: t_{PD} = 5.0 ns (Typ) at V_{CC} = 5 V
- Low Power Dissipation: I_{CC} = 2 μA (Max) at T_A = 25°C
- TTL-Compatible Inputs: V_{IL} = 0.8 V; V_{IH} = 2.0 V
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Designed for 3.0 V to 5.5 V Operating Range
- Low Noise: V_{OLP} = 0.8 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: 48 FETs or 12 Equivalent Gates
- **These devices are available in Pb-free package(s). Specifications herein apply to both standard and Pb-free devices. Please see our website at www.onsemi.com for specific Pb-free orderable part numbers, or contact your local ON Semiconductor sales office or representative.**

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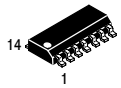
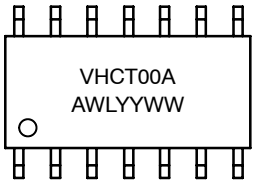
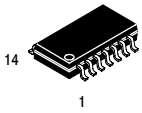
MARKING DIAGRAMS



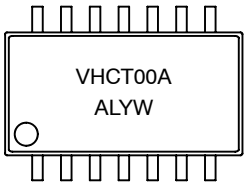
SOIC-14
D SUFFIX
CASE 751A



TSSOP-14
DT SUFFIX
CASE 948G



SOIC EIAJ-14
M SUFFIX
CASE 965



A = Assembly Location
L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MC74VHCT00AD	SOIC-14	48 Units/Rail
MC74VHCT00ADR2	SOIC-14	2500 Units/Reel
MC74VHCT00ADT	TSSOP-14	96 Units/Rail
MC74VHCT00ADTEL	TSSOP-14	2000 Units/Reel
MC74VHCT00ADTR2	TSSOP-14	2000 Units/Reel
MC74VHCT00AM	SOIC EIAJ-14	48 Units/Rail
MC74VHCT00AMEL	SOIC EIAJ-14	2000 Units/Reel

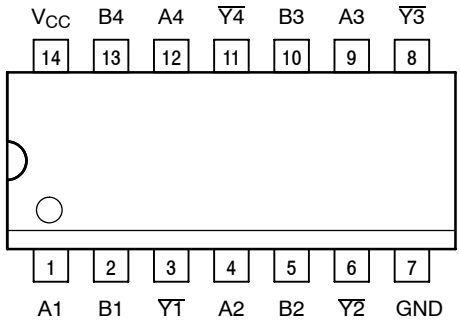


Figure 1. Pin Assignment
(Top View)

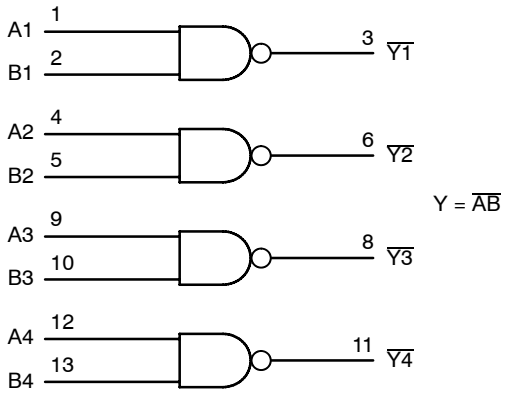


Figure 2. Logic Diagram

PIN ASSIGNMENT	
1	IN A1
2	IN B1
3	OUT $\overline{Y1}$
4	IN A2
5	IN B2
6	OUT $\overline{Y2}$
7	GND
8	OUT $\overline{Y3}$
9	IN A3
10	IN B3
11	OUT $\overline{Y4}$
12	IN A4
13	IN B4
14	V_{CC}

FUNCTION TABLE

Inputs		Output
A	**B**	$\overline{\mathbf{Y}}$
L	L	H
L	H	H
H	L	H
H	H	L

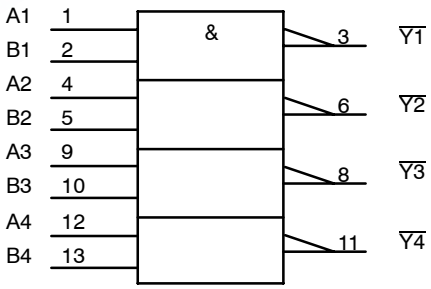


Figure 3. IEC LOGIC DIAGRAM

MAXIMUM RATINGS (Note 1)

Symbol	Characteristics		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +7.0	V
V_{IN}	DC Input Voltage		−0.5 to +7.0	V
V_{OUT}	DC Output Voltage	V_{CC} = 0 High or Low State	−0.5 to 7.0 −0.5 to V_{CC} + 0.5	V
I_{IK}	Input Diode Current		−20	mA
I_{OK}	Output Diode Current	V_{OUT} < GND; V_{OUT} > V_{CC}	+20	mA
I_{OUT}	DC Output Current, per Pin		+25	mA
I_{CC}	DC Supply Current, V_{CC} and GND		+50	mA
P_D	Power Dissipation in Still Air,	SOIC Packages (Note 2) TSSOP Package (Note 2)	500 450	mW
T_L	Lead temperature, 1 mm from case for 10 s		260	°C
T_{stg}	Storage temperature		−65 to +150	°C
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 3) Machine Model (Note 4) Charged Device Model (Note 5)	> 2000 > 200 > 3000	V
$I_{Latch-Up}$	Latch−Up Performance (Note 6)	Above V_{CC} and Below GND at 125°C	±300	mA

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high−impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

* Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute−maximum−rated conditions is not implied.

1. Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute−maximum−rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.
2. Derating − SOIC Packages: −7 mW/°C from 65° to 125°C
   − TSSOP Package: −6.1 mW/°C from 65° to 125°C
3. Tested to EIA/JESD22−A114−A
4. Tested to EIA/JESD22−A115−A
5. Tested to JESD22−C101−A
6. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics		Min	Max	Unit
V_{CC}	DC Supply Voltage		3.0	5.5	V
V_{IN}	DC Input Voltage		0.0	5.5	V
V_{OUT}	DC Output Voltage	VCC = 0 High or Low State	0.0 0.0	5.5 V_{CC}	V
T_A	Operating Temperature Range		−55	+125	°C
t_r , t_f	Input Rise and Fall Time	V_{CC} = 3.3 V ± 0.3 V V_{CC} = 5.0 V ± 0.5 V	0 0	100 20	ns/V

The θ_{JA} of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

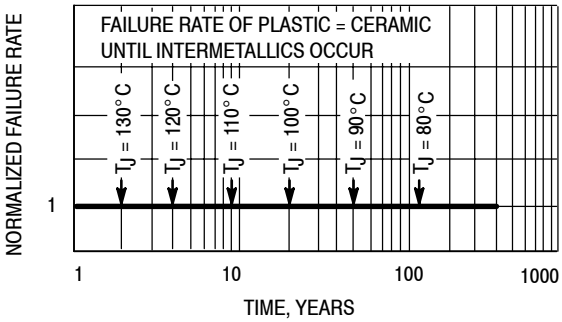


Figure 4. Failure Rate vs. Time Junction Temperature

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V_{CC} (V)	T_A = 25°C Min	T_A = 25°C Typ	T_A = 25°C Max	$T_A \le 85°C$ Min	$T_A \le 85°C$ Max	$T_A \le 125°C$ Min	$T_A \le 125°C$ Max	Unit
V_{IH}	Minimum High−Level Input Voltage		3.0 4.5 5.5	1.4 2.0 2.0			1.4 2.0 2.0		1.4 2.0 2.0		V
V_{IL}	Maximum Low−Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	V
V_{OH}	Minimum High−Level Output Voltage V_{IN} = V_{IH} or V_{IL}	V_{IN} = V_{IH} or V_{IL} I_{OH} = −50 μA	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V
		V_{IN} = V_{IH} or V_{IL} I_{OH} = −4 mA I_{OH} = −8 mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
V_{OL}	Maximum Low−Level Output Voltage V_{IN} = V_{IH} or V_{IL}	V_{IN} = V_{IH} or V_{IL} I_{OL} = 50 μA	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
		V_{IN} = V_{IH} or V_{IL} I_{OL} = 4 mA I_{OL} = 8 mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I_{IN}	Maximum Input Leakage Current	V_{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μA
I_{CC}	Maximum Quiescent Supply Current	V_{IN} = V_{CC} or GND	5.5			2.0		20		40	μA
I_{CCT}	Quiescent Supply Current	Input: V_{IN} = 3.4 V	5.5			1.35		1.50		1.65	mA
I_{OPD}	Output Leakage Current	V_{OUT} = 5.5 V	0.0			0.5		5.0		10	μA

AC ELECTRICAL CHARACTERISTICS C_{load} = 50 pF, Input $t_r = t_f$ = 3.0 ns

Symbol	Parameter	Test Conditions		T_A = 25°C Min	T_A = 25°C Typ	T_A = 25°C Max	$T_A \le$ 85°C Min	$T_A \le$ 85°C Max	$T_A \le$ 125°C Min	$T_A \le$ 125°C Max	Unit
t_{PLH}, t_{PHL}	Maximum Propogation Delay, Input A or B to Y	V_{CC} = 3.3 ± 0.3 V	C_L = 15 pF		4.1	10.0		11.0		13.0	ns
			C_L = 50 pF		5.5	13.5		15.0		17.5	
		V_{CC} = 5.0 ± 0.5 V	C_L = 15 pF		3.1	6.9		8.0		9.5	
			C_L = 50 pF		3.6	7.9		9.0		10.5	
C_{IN}	Maximum Input Capacitance				5.5	10		10		10	pF

		Typical @ 25°C, V_{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Note 7)	17	pF

7. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no−load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

NOISE CHARACTERISTICS (Input $t_r = t_f$ = 3.0ns, C_L = 50pF, V_{CC} = 5.0V, Measured in SO Package)

Symbol	Characteristic	T_A = 25°C Typ	T_A = 25°C Max	Unit
V_{OLP}	Quiet Output Maximum Dynamic V_{OL}	0.4	0.8	V
V_{OLV}	Quiet Output Minimum Dynamic V_{OL}	− 0.4	− 0.8	V
V_{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V_{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

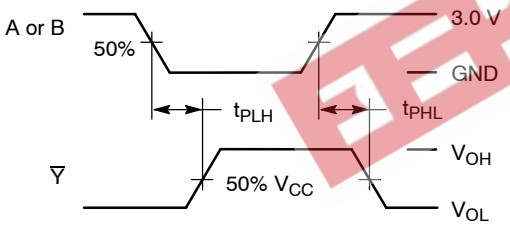
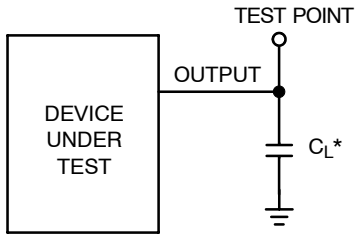


Figure 5. Switching Waveforms



*Includes all probe and jig capacitance

Figure 6. Test Circuit

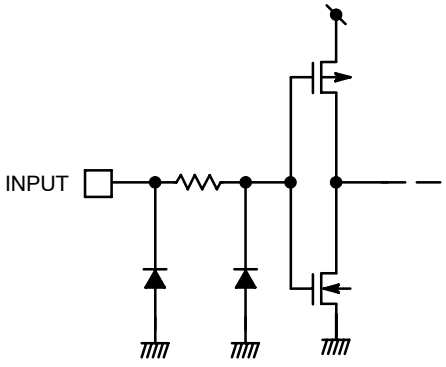
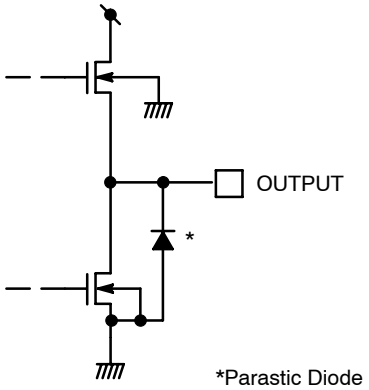


Figure 7. Input Equivalent Circuit

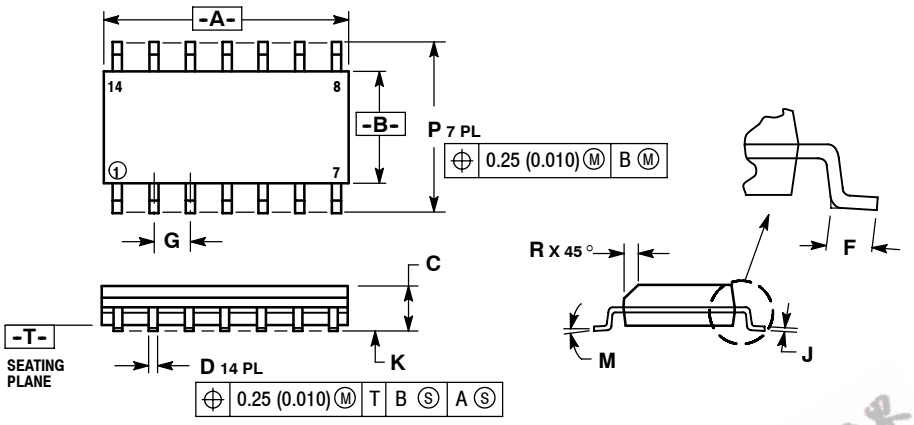


*Parastic Diode

Figure 8. Output Equivalent Circuit

PACKAGE DIMENSIONS

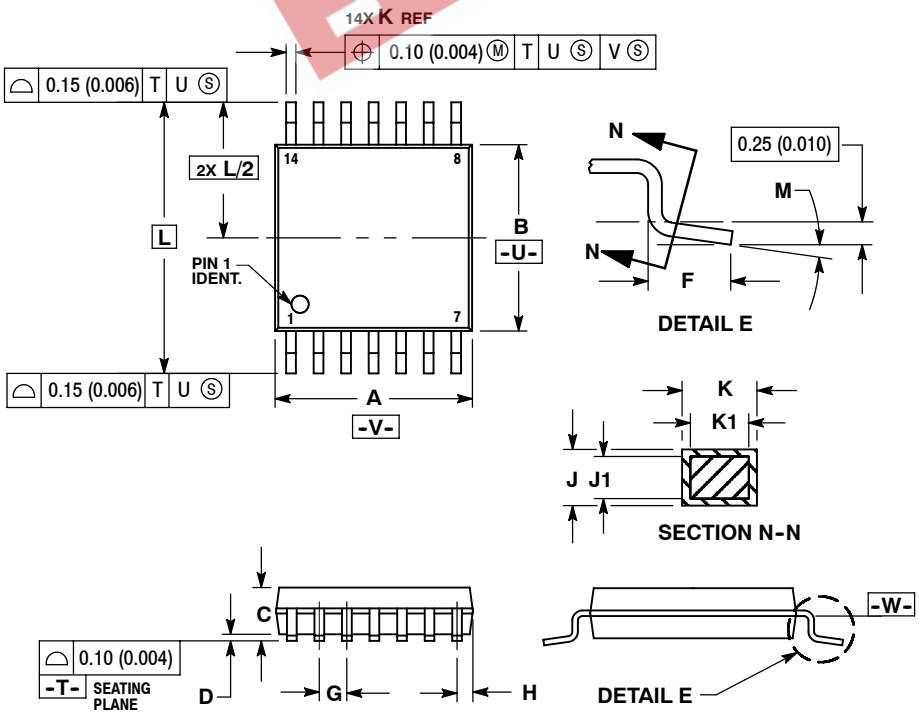
D SUFFIX
SOIC PACKAGE
CASE 751A−03
ISSUE F



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7 °	0 °	7 °
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

DT SUFFIX
TSSOP PACKAGE
CASE 948G−01
ISSUE O

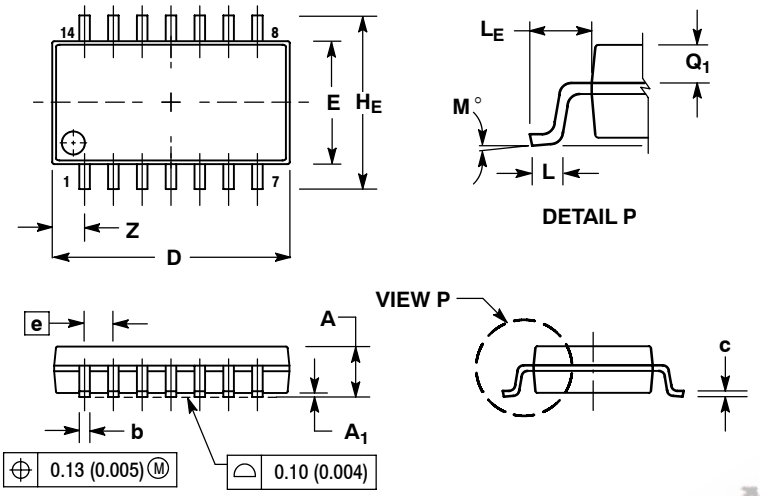


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

MC74VHCT00A

M SUFFIX
SOIC EIAJ PACKAGE
CASE 965-01
ISSUE O



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A_1	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H_E	7.40	8.20	0.291	0.323
0.50	0.50	0.85	0.020	0.033
L_E	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
Q_1	0.70	0.90	0.028	0.035
Z	---	1.42	---	0.056

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